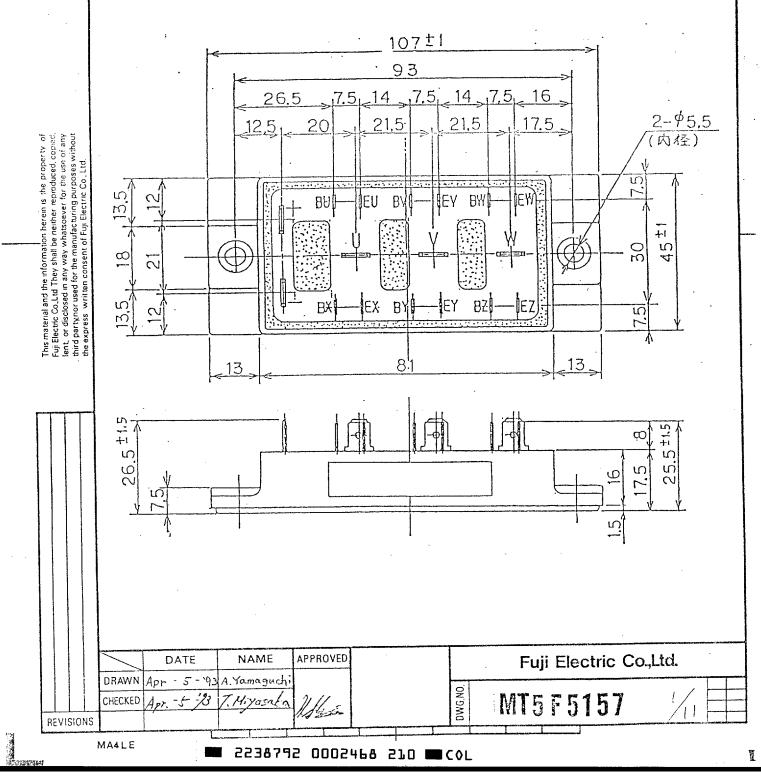
6 M B I 2 5 J - 1 2 0 (TENTATIVE)

1. Outline Drawing

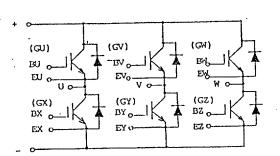
Unit: mm

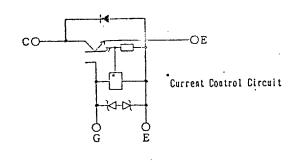
* Isolation Voltage : AC 2500 V 1 minute



2. Equivalent Circuit

3. Equivalent Circuit





4. Absolute Maximum Ratings

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(Tj=25°C)

Items		Symbols	Ratings	Units
Collector-emitter voltage		VcEs	1 2 0 0	V
Gate -emitter voltage		VGES	± 2. 0	V
Continuous		Ic	2 5	
Collector	1 ms	Ic pulse	5 0	
current 1 ms		- I c	2 5	A
		-Ic pulse	5 0	
Max.power dissipation		PC	1 6 0	W
Operating temperature		Тј	+ 1 5 0	•C
Storage temperature		Tstg	-40 ∼ +125	*C
Isolation voltage		Vis	AC 2500 (1 min)	V
Screw Torque		Mounting * 1	3. 5	. N • m

Note: *1 Recommendable Value : 2.5 \sim 3.5 N·m (M5)

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5. Static electrical characteristics

(at Tj=25°C unless otherwise specified)

	Symbols	Cha	racterist	tics	Conditions		Units
Items		min.	typ.	max.			
Zero gate voltage	Ices			1.0	Tj= 25°C	V G E = 0V	m A
collector current					Tj=125°C	V ce = 1200V	m A
Gate-emitter	_			15	V c = (O Y	μA
leakage current	IGES				V G E = 3	± 2 0 V	
Gate-emitter threshold Very voltage	Vge (th)		F A		$V_{CE} = 2 0 V$ $I_{C} = 2 5 \text{ mA}$	20 V	v
		-	5.0				
Collector-emitter					V _{G E} =	1 5 V	v
saturation voltage	saturation Vce(sat)		2.2		1 c =	2 5 A	· · · · · · · · · · · · · · · · · · ·

6. Dynamic ratings (at Tj=25°C unless otherwise specified)

		Characteristics			Conditions	Units
Items	· Symbols	min.	typ.	max.	Conditions	
Input capacitance	Cies		3000		$V_{GE} = 0 V$	
Output capacitance	Coes				V _{CE} = 1 0 V	рF
Reverse transfer capacitance	Cres	,		·	f = 1 MIIz	
	ton		0.65		$V_{cc} = 600V$	
Turn-on time	tr		0.30		$\begin{array}{c} I_{C} = 25A \\ V_{GE} = \pm 15V \end{array}$	μs
Turn-off time	toff		0.90		$R_{\rm G} = 50\Omega$	·
	tf		0.20			

7. Characteristics of reverse diode (at Tj=25 °C unless otherwise specified)

		Characteristics			Conditions	Units
Items	Symbols	min.	typ.	max.	Conditions	
Diode forward on-voltage	VF		2.5		$1 F = 25A$ $V_{GE} = 0V$	V
Reverse recovery	trr			350	I F = 25A -di/dt = 75A/μs	ns

8. Thermal resistance characteristics

Items		Cha	racteris	tics	Condițions	Units
	Symbols	min.	typ.	max.		
	Rth(j-c)			0.781	IGBT	_
Thermal resistance	Rth(j-c)			1.870	Diode	c/w
	* Rth(c-f)		0.05		the base to cooling fin	

X This is the value which is defined mounting on the additional cooling fin with thermal compound.

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